

AMENDMENTS TO THE CLAIMS

Claim 1 (Currently Amended): A high concentration silica slurry, consisting of:
a fumed silica powder dispersed in a solvent,
said solvent consisting of at least one selected from the group consisting of water and alcohols,

said silica slurry having a silica concentration of more than 50 % by weight and a viscosity of less than 1000 mPa·s,

wherein said silica powder has a ratio DL/DT of less than 1.3, wherein DL is an average particle size of the silica powder measured by a laser diffraction particle size distribution method and DT is an average primary particle size of the silica powder measured by a TEM photography observation,

wherein a ratio B/A is less than 1.5, where A is the viscosity of the slurry measured at the time of preparing and B is the viscosity after one month, and

wherein said silica powder has a uniform particle size and an average primary particle size of from 0.08 μ m to 0.8 μ m.

Claim 2 (Original): The high concentration silica slurry according to Claim 1, wherein the silica concentration is from more than 70 % by weight to less than 80 % by weight and the viscosity is less than 800 mPa·s at the time of preparing.

Claims 3-4 (Canceled)

Claim 5 (Original): The high concentration silica slurry according to Claim 1, wherein said solvent is water.

Claim 6 (Canceled)

Claim 7 (Previously Presented): A polishing composite, comprising:
the high concentration silica slurry of Claim 1.

Claim 8 (Original): The polishing composite according to Claim 7, wherein the silica concentration is from more than 70 % by weight to less than 80 % by weight and the viscosity is less than 800 mPa•s at the time of preparing.

Claim 9 (Canceled)

Claim 10 (Original): The polishing composite according to Claim 7, wherein the impurity concentrations of said silica powder are less than 1.0 ppm of each of sodium and potassium, less than 1.0 ppm of aluminum, and less than 5 ppm of each of sulfur, nickel, chromium, and iron.

Claim 11 (Original): The polishing composite according to Claim 7, wherein said solvent is water.

Claim 12 (Canceled)

Claim 13 (Previously Presented): A process for polishing a substrate, comprising:
contacting the surface of said substrate with the slurry of Claim 1.

Claim 14 (Original): The process according to Claim 13, wherein said substrate is a silicon wafer.

Claim 15 (Original): The process according to Claim 13, wherein the silica concentration is from more than 70 % by weight to less than 80 % by weight and the viscosity is less than 800 mPa•s at the time of preparing.

Claim 16 (Canceled)

Claim 17 (Original): The process according to Claim 13, wherein impurity concentrations of said silica powder are less than 1.0 ppm of each of sodium and potassium, less than 1.0 ppm of aluminum, and less than 5 ppm of each of sulfur, nickel, chromium, and iron.

Claim 18 (Original): The process according to Claim 13, wherein said solvent is water.

Claim 19 (Canceled)

Claim 20 (Original): The process according to Claim 13, wherein said substrate is a semiconductor material.

Claim 21 (Previously Presented): The high concentration silica slurry according to Claim 1, wherein impurity concentrations of said silica powder are less than 1.0 ppm of each of sodium and potassium, less than 1.0 ppm of aluminum, and less than 5 ppm of each of sulfur, nickel, chromium, and iron.

Claim 22 (Previously Presented): The high concentration silica slurry according to Claim 1, wherein the water is distilled water.

Claim 23 (Previously Presented): The high concentration silica slurry according to Claim 1, wherein the alcohols are alcohols having from 1 to 4 carbon atoms.

Claim 24 (Previously Presented): The high concentration silica slurry according to Claim 1, wherein the solvent consists of at least one selected from the group consisting of distilled water and alcohols having from 1 to 4 carbon atoms.